

*D1260

*PSPICE MODEL FOR POINT NINE RF N-CHANNEL VERTICAL DMOS POWER FET

*May 2004

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*          _____GATE
*          I          _____DRAIN
*          I   I          _____SOURCE
*          I   I   I
.SUBCKT D1260 10 20 30
*Cin1,Cin2 & Lin model the input side of the package
Cin1 10 30 0.32p
Lin 10 11 0.59n
Cin2 11 30 0.32p

LG 11 12 2n ;Gate bond wire inductance
CGS 12 13 182.8p ;Gate-source capacitance
MOS 14 12 13 13 D1260 L=0.9U W=0.224 ;D G S B LEVEL1
JFET 16 13 14 D1260 ;D G S
DBODY 13 16 D1260 ;P N
LS 13 30 0.3n ;Source bond wire inductance
CGD 12 16 13.2p ;Gate-drain feedback capacitance
*Cout1,Cout2 & Lout model the output side of the package
Cout1 16 30 1.05p
Lout 16 20 1.77n
Cout2 20 30 1.05p

.MODEL D1260 NMOS (VTO=4.68 KP=2.687E-5 LAMBDA=0.01 RD=0.003 RS=0.09)
.MODEL D1260 NJF (VTO=-4.97 BETA=3.04 LAMBDA=3.385)
.MODEL D1260 D (CJO=552.4P RS=0.82 VJ=0.7 M=0.33 BV=50)

.ENDS
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